

IN THE SPECIFICATION:

Please replace paragraph number [0004] with the following rewritten paragraph:

[0004] “Flip-chip” technology, one example of which is termed controlled collapse chip connection (C-4) technology, is an example of a packaging and assembly technology that results in a semiconductor device being oriented substantially parallel to a carrier substrate, such as a circuit board. In flip-chip technology, the bond pads or contact pads of a semiconductor device are arranged in an array over a major surface of the semiconductor device. Flip-chip techniques are applicable to both bare and packaged semiconductor devices. A packaged flip-chip type semiconductor device, which, when an array of discrete conductive elements is located over the major surface, is referred to in the art as a “ball grid array” (BGA) package, typically includes a semiconductor die and a substrate, which is typically termed an ~~“interposer”~~ “interposer.”

Please replace paragraph number [0035] with the following rewritten paragraph:

[0035] The material from which tape 20 is formed preferably exhibits a similar coefficient of thermal expansion (CTE) to that of the material of semiconductor die 10. For example, a polyimide tape 20 would be useful with a semiconductor die 10 formed on a silicon substrate element. When semiconductor die 10 and tape 20 have substantially similar, or ~~“matched”~~, “matched,” coefficients of thermal expansion, the likelihood that these elements of a package will be mechanically stressed during thermal cycling occurring in testing or operation of semiconductor die 10 is reduced.

Please replace paragraph number [0050] with the following rewritten paragraph:

[0050] Once encapsulant material 52 has hardened, all or a portion of coverlay 42, 42' may be removed from substrate element 30, 30" so as to expose at least contact pads 38, 38', 38" thereof, as depicted in FIGs. 7, 7A, and 7B, and form an operable semiconductor device package 2, 2', 2".